**Product data sheet** 

# 1. General description

Hyperfast power diode in a SOD113A (2-lead TO-220F) plastic package.

### 2. Features and benefits

- · Low reverse recovery current
- Low thermal resistance
- Low leakage current
- Reduces switching losses in associated MOSFET or IGBT

# 3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

## 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			6	000		V
$I_{F(AV)}$	average forward current	$δ = 0.5$ ; square-wave pulse; $T_h \le 97$ °C; Fig. 1; Fig. 2; Fig. 3	5			А	
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_h \le$ 97 °C; square-wave pulse	10			А	
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	60 65		А		
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse			А		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics			,			
$V_{F}$	forward voltage	I <sub>F</sub> = 5 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.35	2.1	V
Dynamic	characteristics			,			
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	11	-	ns

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode		K — A 001aaa020
mb	n.c.	mounting base; isolated		001aaa020

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BYC5X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220F "full pack"	SOD113A		

# 7. Marking

### Table 4. Marking codes

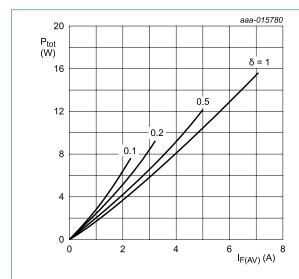
Type number	Marking codes
BYC5X-600P	BYC5X-600P

# 8. Limiting values

#### Table 5. Limiting values

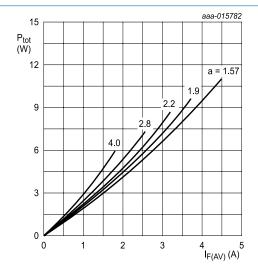
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		600	V
$V_{\text{RWM}}$	crest working reverse voltage		600	V
$V_R$	reverse voltage	DC	600	V
I <sub>F(AV)</sub>	average forward current	$δ = 0.5$ ; square-wave pulse; $T_h \le 97$ °C; Fig. 1; Fig. 2; Fig. 3	5	А
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_h \le 97 °C$ ; square-wave pulse	10	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	60	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	65	А
T <sub>stg</sub>	storage temperature		-65 to 175	°C
T <sub>j</sub>	junction temperature		175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.801 \text{ V; } R_{\text{s}} = 0.062 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

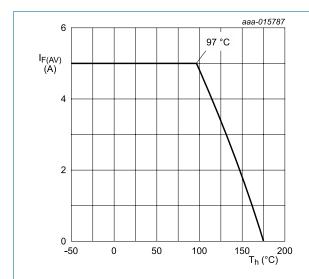


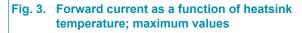
a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 1.801 V;  $R_s$  = 0.062  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

WeEn Semiconductors BYC5X-600P

Hyperfast power diode





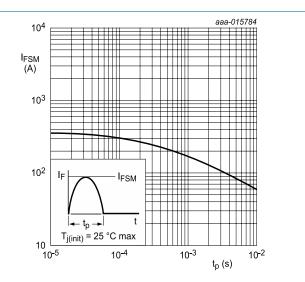
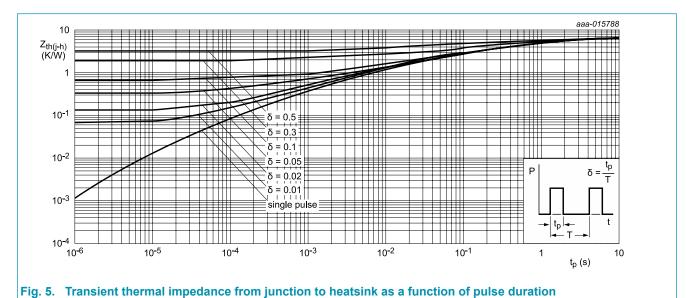


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig 5	-	-	6.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



## 10. Isolation characteristics

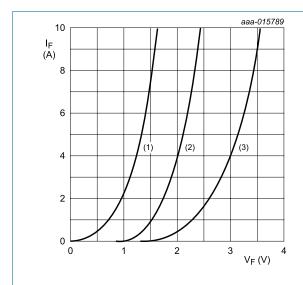
### **Table 7. Isolation characteristics**

Syn	nbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol</sub>	(RMS)	RMS isolation voltage	from all pins to external heatsink; sinusoidal waveform; clean and dust free; $50 \text{ Hz} \le f \le 60 \text{ Hz}$ ; $RH \le 65 \%$	-	-	2500	V
C <sub>isol</sub>	I	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

# 11. Characteristics

Table 8 Characteristics

iable o. Ci	naracteristics					
Symbol	Parameter	Conditions	Miı	n Typ	Max	Unit
Static cha	aracteristics					
$V_{F}$	forward voltage	I <sub>F</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2.5	3.3	V
		I <sub>F</sub> = 5 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.35	2.1	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C	-	-	0.6	mA
Dynamic	characteristics					
Q <sub>r</sub>	recovered charge	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	19	-	nC
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	45	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	11	-	ns
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	23	-	ns
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	28	-	ns
		$I_F = 5 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_J = 25 \text{ °C}; Fig. 7$	-	13	25	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	1.7	-	А
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_i = 125 \text{ °C}; Fig. 7$	-	3.2	-	А
		·  ·== 0, <u>g</u>				



 $V_o = 1.833 \text{ V}; R_s = 0.055 \Omega$ 

(1) T<sub>i</sub> = 150 °C; typical values

(2) T<sub>j</sub> = 150 °C; maximum values

(3)  $T_i = 25$  °C; maximum values

Fig. 6. Forward current as a function of forward voltage

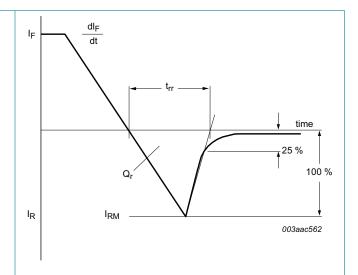
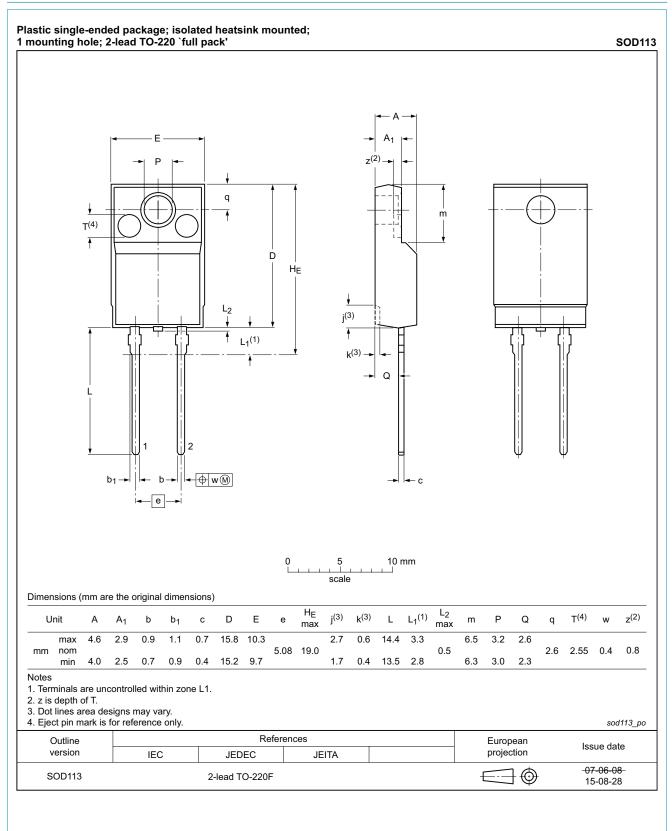


Fig. 7. Reverse recovery definitions; ramp recovery

# 12. Package outline



# 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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